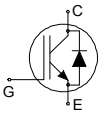
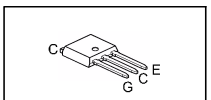
IKD10N60R, IKU10N60R

TRENCHSTOP™ RC-Series for hard switching applications

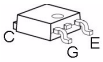
IGBT with integrated diode in packages offering space saving advantage

Features:
TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering
- Optimised V_{CEsat} and V_F for low conduction losses
- Smooth switching performance leading to low EMI levels
- Very tight parameter distribution
- Operating range of 1 to 20kHz
- Maximum junction temperature 175°C
- Short circuit capability of 5µs
- Best in class current versus package size performance
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant (for PG-TO252: solder temperature 260°C, MSL1)
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/





PG-TO251-3 (I-Pak)



PG-TO252-3 (D-Pak)

Applications:
- Consumer motor drives

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IKD10N60R	600V	10A	1.65V	175°C	K10R60	PG-TO252-3
IKU10N60R	600V	10A	1.65V	175°C	K10R60	PG-TO251-3

Maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_C	 20.0 10.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	30.0	A
Turn off safe operating area $V_{CE} \le 600V$, $T_{vj} \le 175°C$	-	30.0	A
Diode forward current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_F	 20.0 10.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	30.0	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time V_{GE} = 15.0V, $V_{CC} \le 400V$, $T_{vj} \le 150°C$ Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s	t_{SC}	5	µs
Power dissipation T_C = 25°C	P_{tot}	150.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	°C
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s for 10 s (according to JEDEC J-STA-020A)	PG-TO251-3 PG-TO252-3	260 260	°C

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		1.00	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		2.60	K/W
Thermal resistance, min. footprint junction - ambient	$R_{th(j-a)}$	PG-TO252-3	75	K/W
Thermal resistance, 6cm² Cu on PCB junction - ambient	$R_{th(j-a)}$	PG-TO252-3	50	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$	PG-TO251-3	75	K/W

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.20mA	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 10.0A T_{vj} = 25°C T_{vj} = 175°C	 - -	 1.65 1.85	 2.10 -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 10.0A T_{vj} = 25°C T_{vj} = 175°C	 - -	 1.70 1.70	 2.10	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.17mA, V_{CE} = V_{GE}	4.3	5.0	5.7	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 600V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	 - -	 - -	 40.0 1000.0	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 10.0A	-	6.1	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{iss}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	655	-	pF
Output capacitance	C_{oss}		-	37	-	
Reverse transfer capacitance	C_{rss}		-	22	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 10.0A, V_{GE} = 15V	-	64.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	PG-TO252-3 PG-TO251-3	-	- 7.0	-	nH

Switching Characteristic, Inductive Load, at T_{vj} = 25°C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 10.0A, V_{GE} = 0.0/15.0V, r_G = 23.0Ω, L_σ = 60nH, C_σ = 40pF L_σ, C_σ from Fig. E	-	14	-	ns
Rise time	t_r		-	10	-	ns
Turn-off delay time	$t_{d(off)}$		-	192	-	ns
Fall time	t_f		-	139	-	ns
Turn-on energy	E_{on}		-	0.21	-	mJ
Turn-off energy	E_{off}		-	0.38	-	mJ
Total switching energy	E_{ts}		-	0.59	-	mJ

Anti-Parallel Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 10.0A, di_F/dt = 1000A/µs	-	62	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.56	-	µC
Diode peak reverse recovery current	I_{rrm}		-	20.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-260	-	A/µs

Switching Characteristic, Inductive Load, at T_{vj} = 175°C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 10.0A, V_{GE} = 0.0/15.0V, r_G = 23.0Ω, L_σ = 60nH, C_σ = 40pF L_σ, C_σ from Fig. E	-	13	-	ns
Rise time	t_r		-	11	-	ns
Turn-off delay time	$t_{d(off)}$		-	217	-	ns
Fall time	t_f		-	211	-	ns
Turn-on energy	E_{on}		-	0.35	-	mJ
Turn-off energy	E_{off}		-	0.58	-	mJ
Total switching energy	E_{ts}		-	0.93	-	mJ

Anti-Parallel Diode Characteristic, at T_{vj} = 175°C

Diode reverse recovery time	t_{rr}	T_{vj} = 175°C, V_R = 400V, I_F = 10.0A, di_F/dt = 1000A/µs	-	98	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.22	-	µC
Diode peak reverse recovery current	I_{rrm}		-	20.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-259	-	A/µs

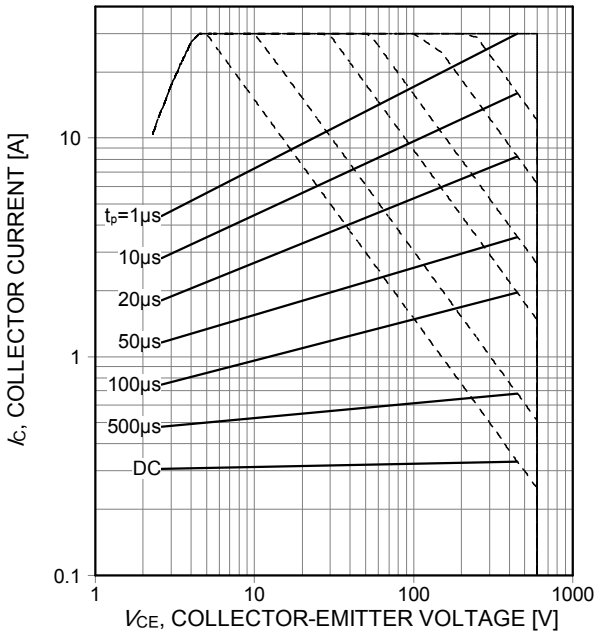


Figure 1. Forward bias safe operating area
(D=0, T_C=25°C, T_{vj}≤175°C; V_{GE}=15V)

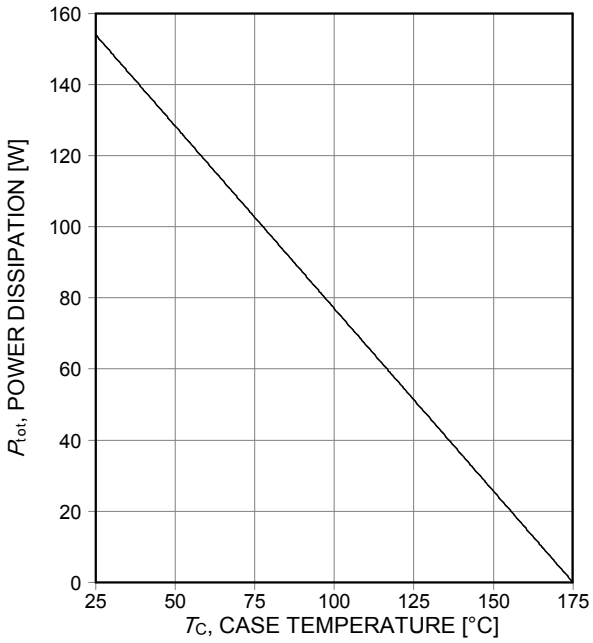


Figure 2. Power dissipation as a function of case temperature
(T_{vj}≤175°C)

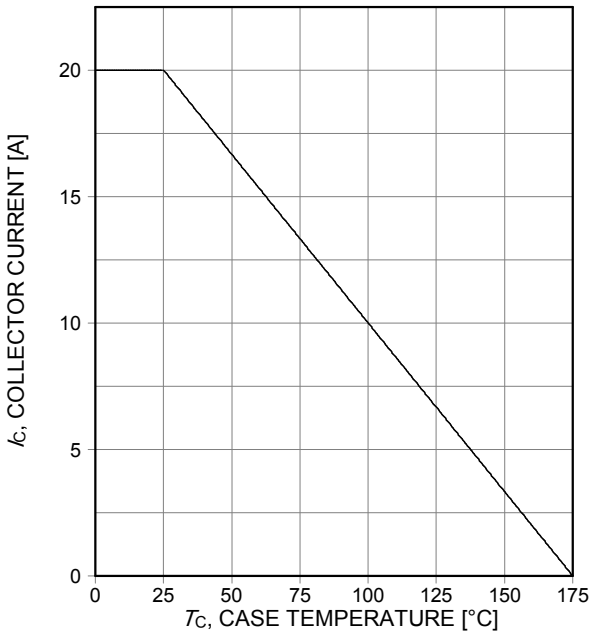


Figure 3. Collector current as a function of case temperature
(V_{GE}≥15V, T_{vj}≤175°C)

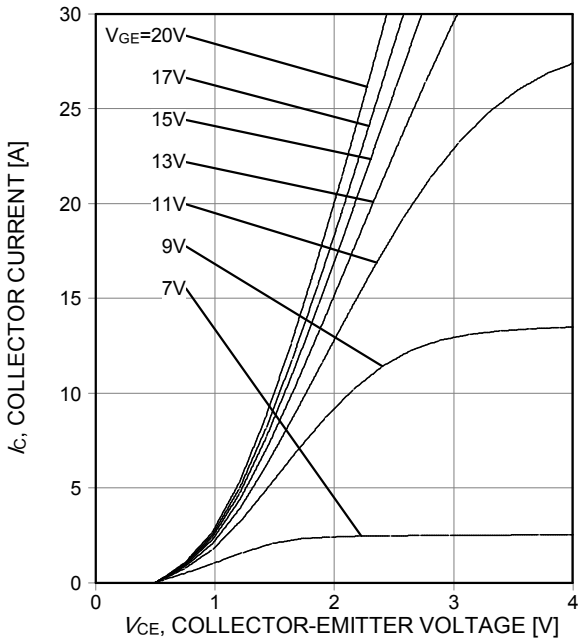


Figure 4. Typical output characteristic
(T_{vj}=25°C)

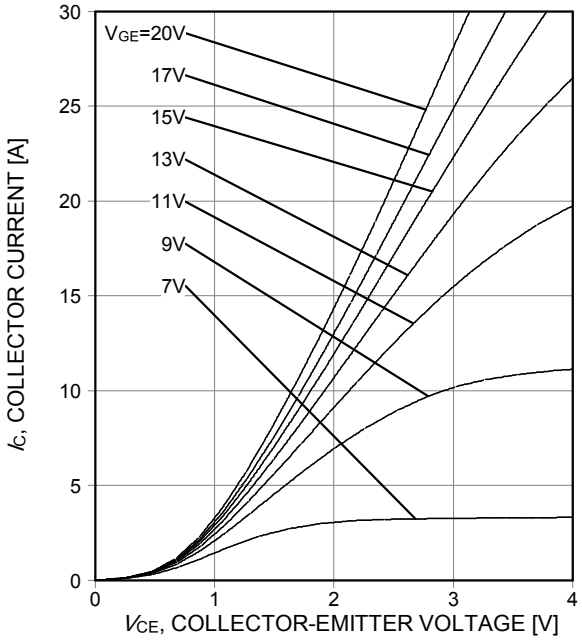


Figure 5. Typical output characteristic
(T_{vj}=175°C)

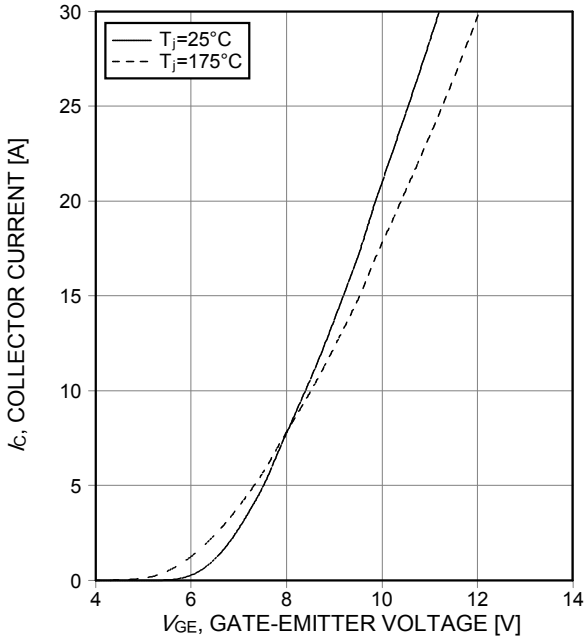


Figure 6. Typical transfer characteristic
(V_{CE}=10V)

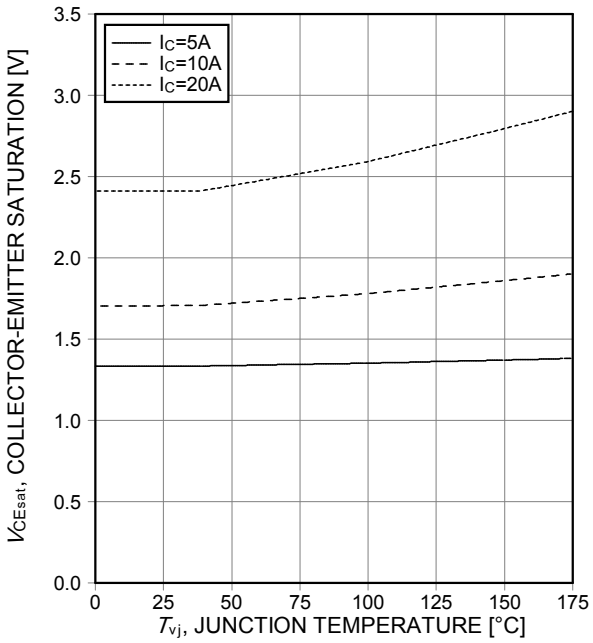


Figure 7. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE}=15V)

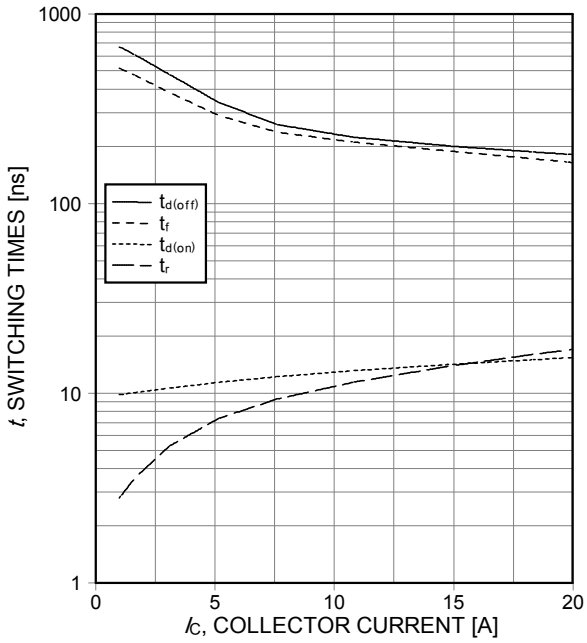


Figure 8. Typical switching times as a function of collector current
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=15/0V, r_G=23Ω, Dynamic test circuit in Figure E)

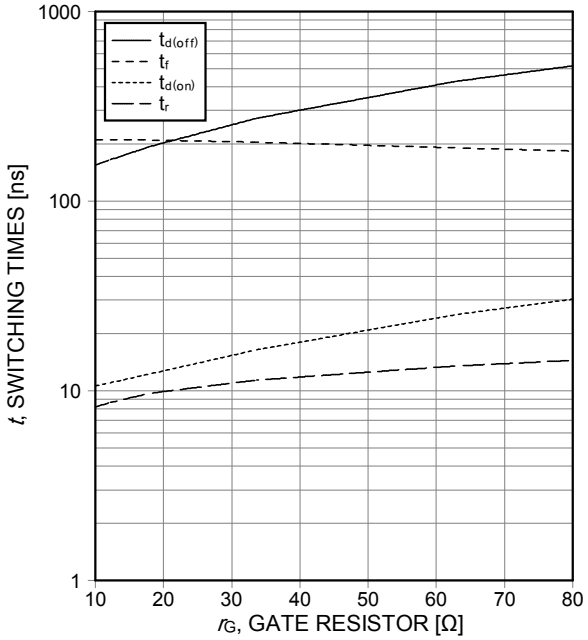


Figure 9. Typical switching times as a function of gate resistor
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=10A, Dynamic test circuit in Figure E)

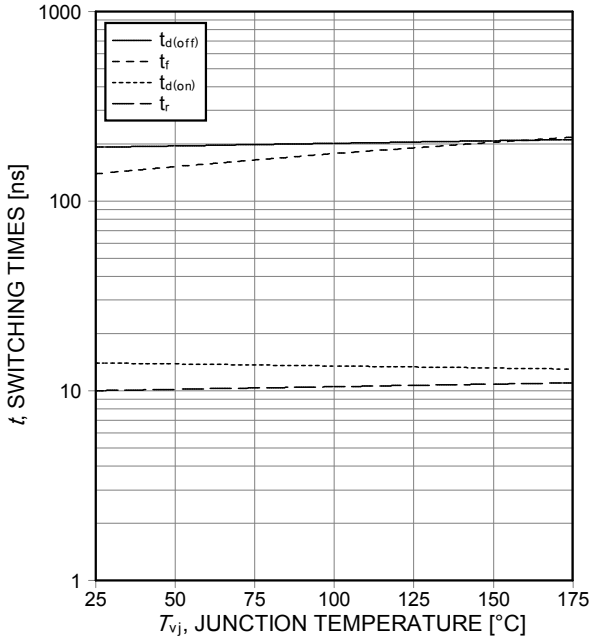


Figure 10. Typical switching times as a function of junction temperature
(inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=10A, r_G=23Ω, Dynamic test circuit in Figure E)

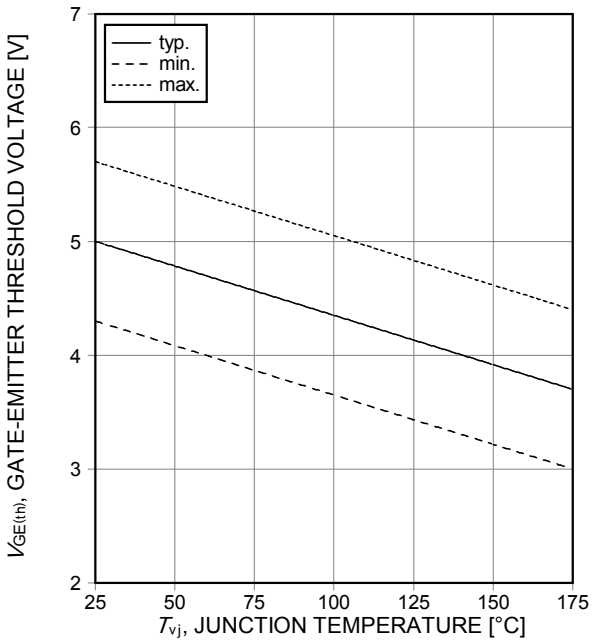


Figure 11. Gate-emitter threshold voltage as a function of junction temperature
(I_C=0.17mA)

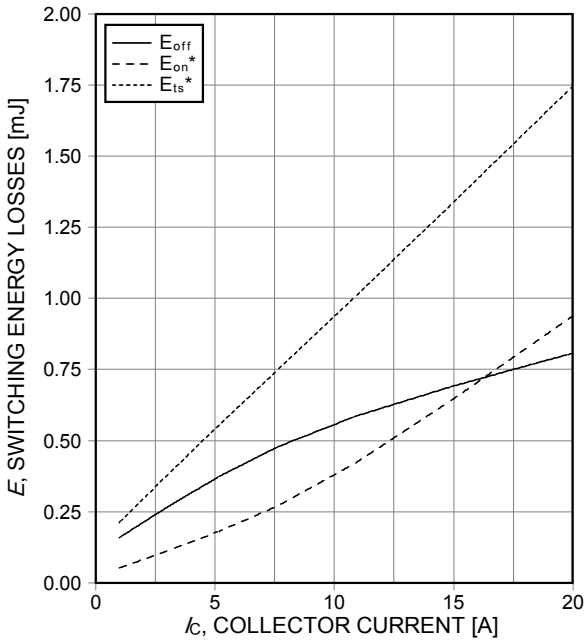


Figure 12. Typical switching energy losses as a function of collector current
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=15/0V, r_G=23Ω, Dynamic test circuit in Figure E)

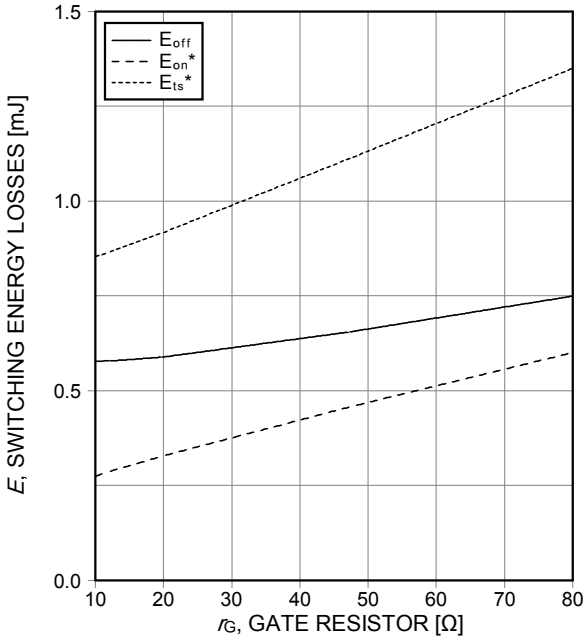


Figure 13. Typical switching energy losses as a function of gate resistor
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=10A, Dynamic test circuit in Figure E)

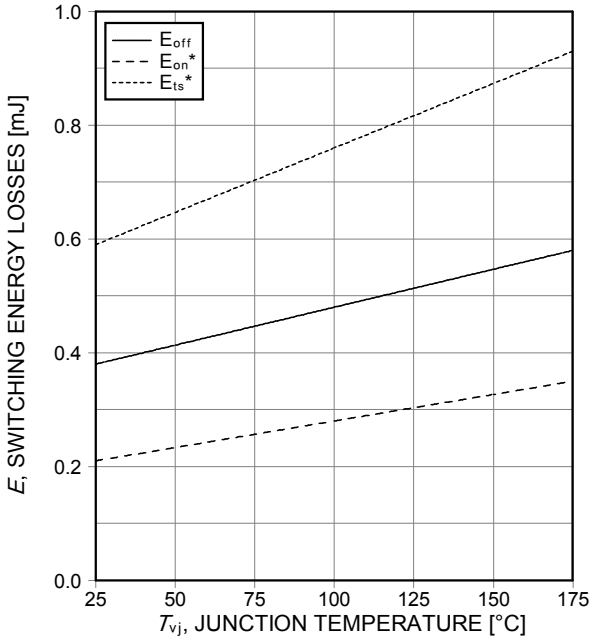


Figure 14. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=10A, r_G=23Ω, Dynamic test circuit in Figure E)

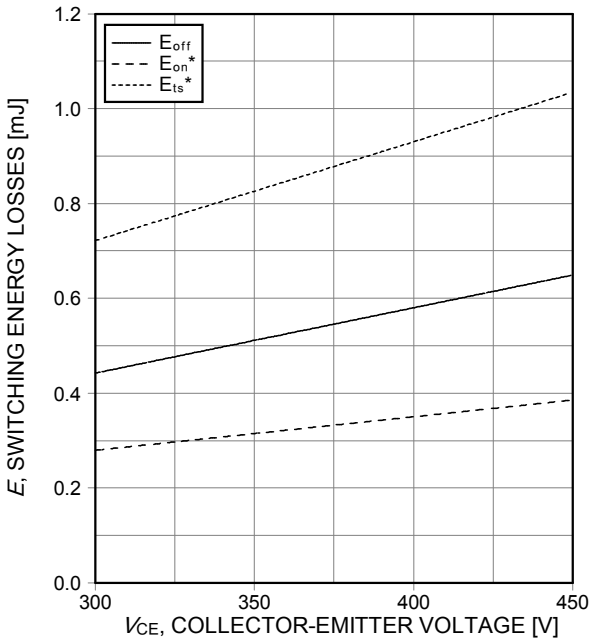


Figure 15. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_{vj}=175°C, V_{GE}=15/0V, I_C=10A, r_G=23Ω, Dynamic test circuit in Figure E)

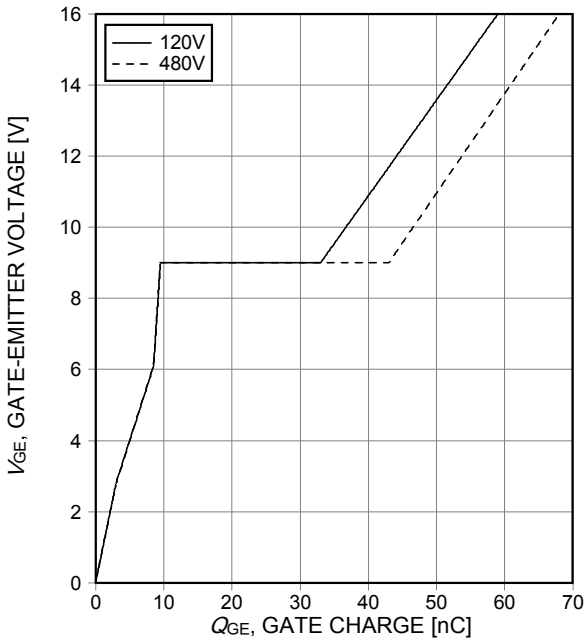


Figure 16. Typical gate charge
(I_C=10A)

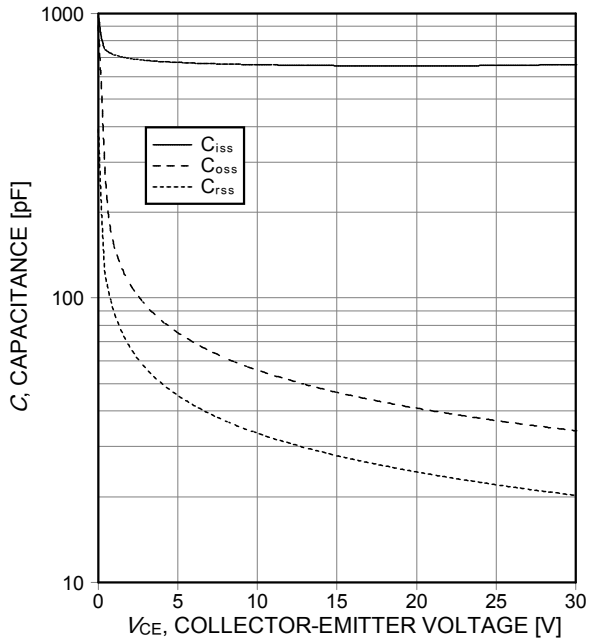


Figure 17. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f=1MHz)

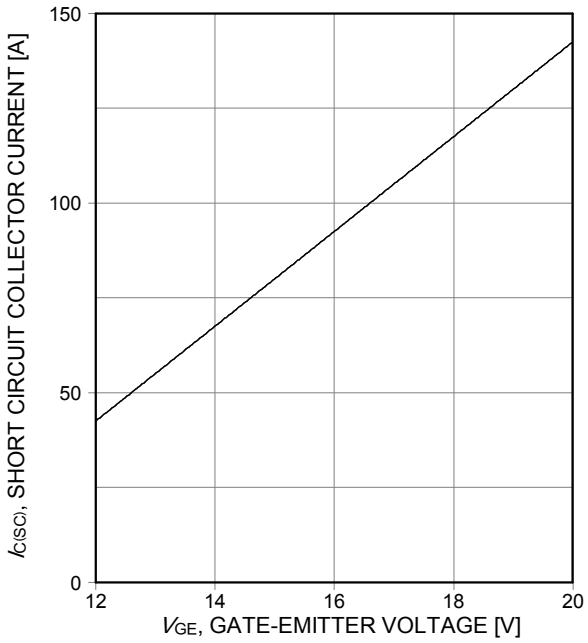


Figure 18. Typical short circuit collector current as a function of gate-emitter voltage
(V_{CE}≤400V, start at T_{vj}=25°C)

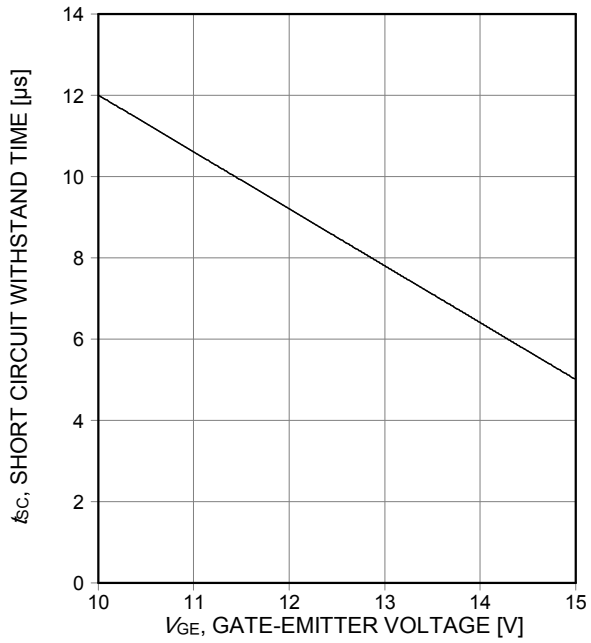


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}≤400V, start at T_{vj}≤150°C)

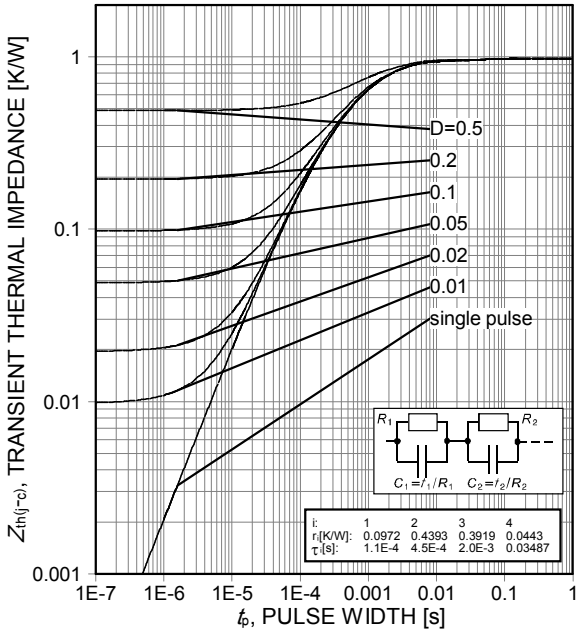


Figure 20. IGBT transient thermal impedance as a function of pulse width [1)]
(D=t_p/T)

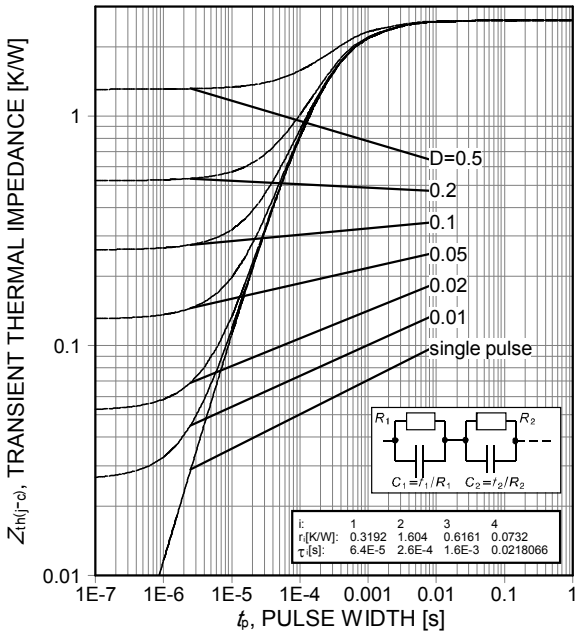


Figure 21. Diode transient thermal impedance as a function of pulse width [1)]
($D=t_p/T$)

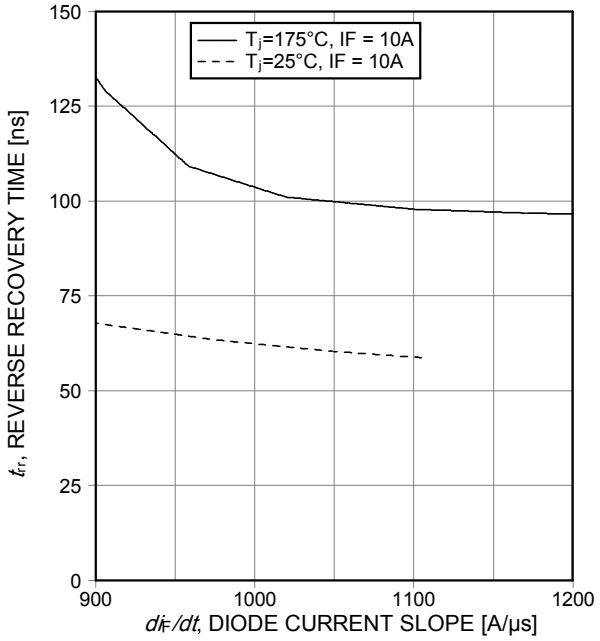


Figure 22. Typical reverse recovery time as a function of diode current slope
(V_R=400V)

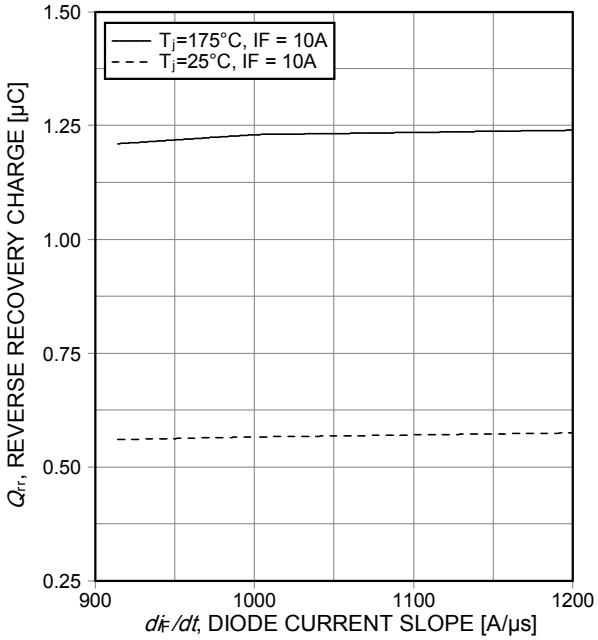


Figure 23. Typical reverse recovery charge as a function of diode current slope
(V_R=400V)

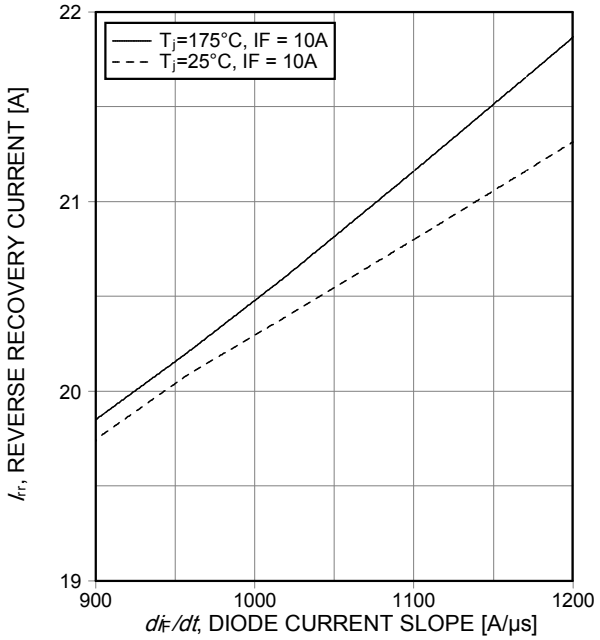


Figure 24. Typical reverse recovery current as a function of diode current slope
(V_R=400V)

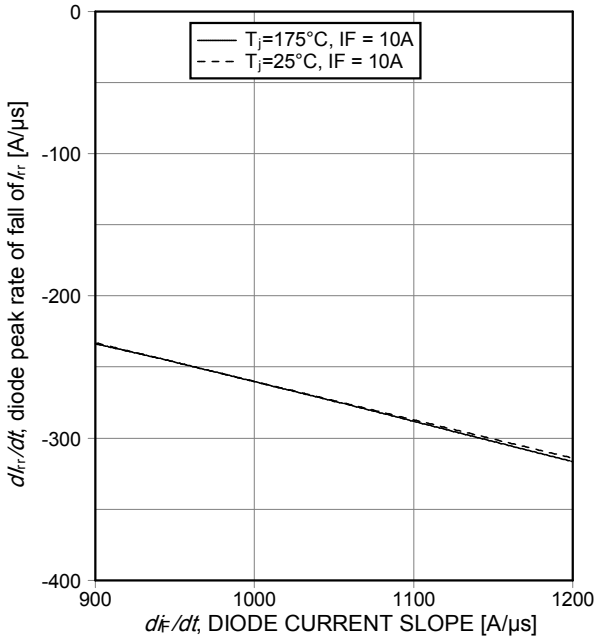


Figure 25. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=400V)

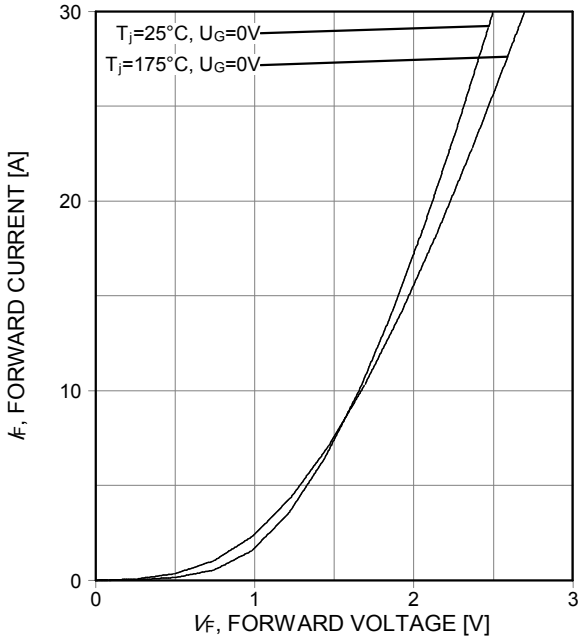


Figure 26. Typical diode forward current as a function of forward voltage

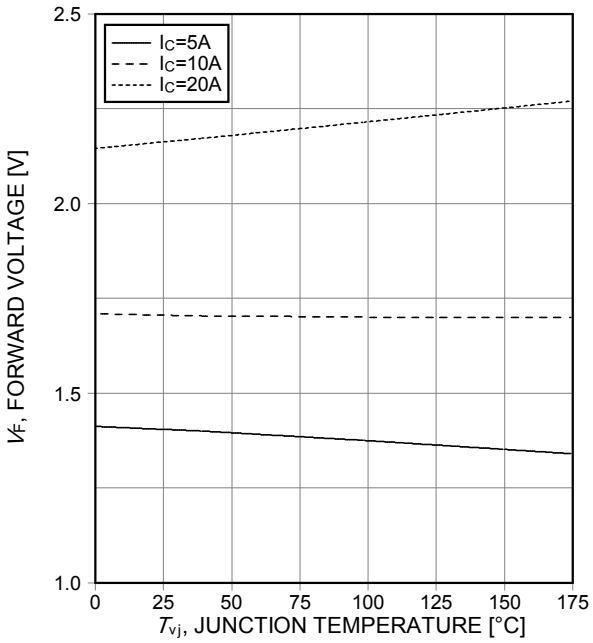
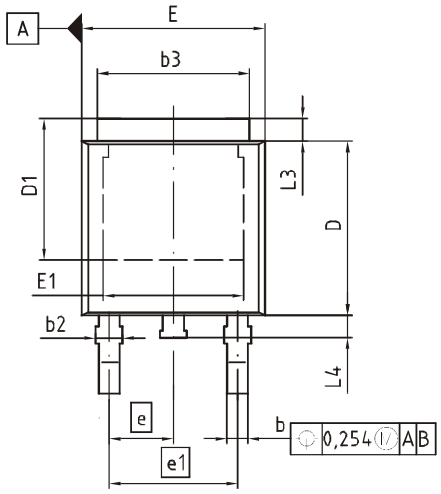
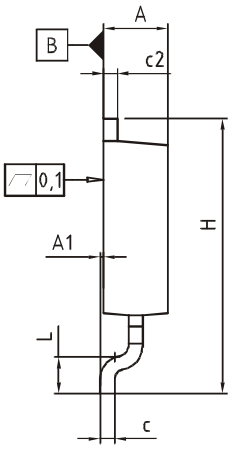
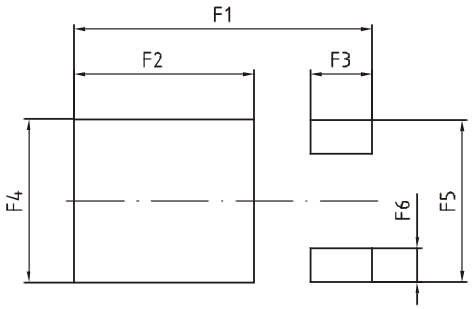


Figure 27. Typical diode forward voltage as a function of junction temperature

TO252-3-1/-11/-21/-311/-341







DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

DOCUMENT NO.
Z8B00003328

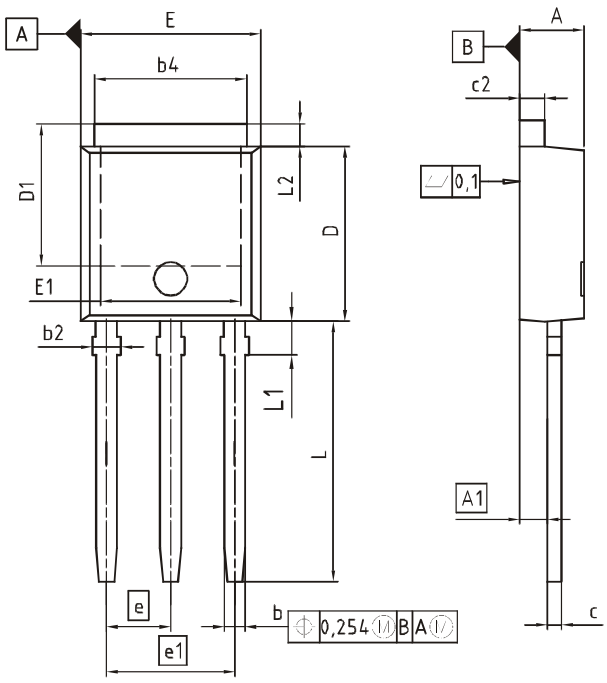
SCALE 0 2.0 0 2.0 4mm

EUROPEAN PROJECTION

ISSUE DATE
19-10-2007

REVISION
03

TO251-3-21/-341



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

DOCUMENT NO.
Z8B00003330

SCALE
0
2.0
0 2.0
4mm

EUROPEAN PROJECTION

ISSUE DATE
19-03-2008

REVISION
03

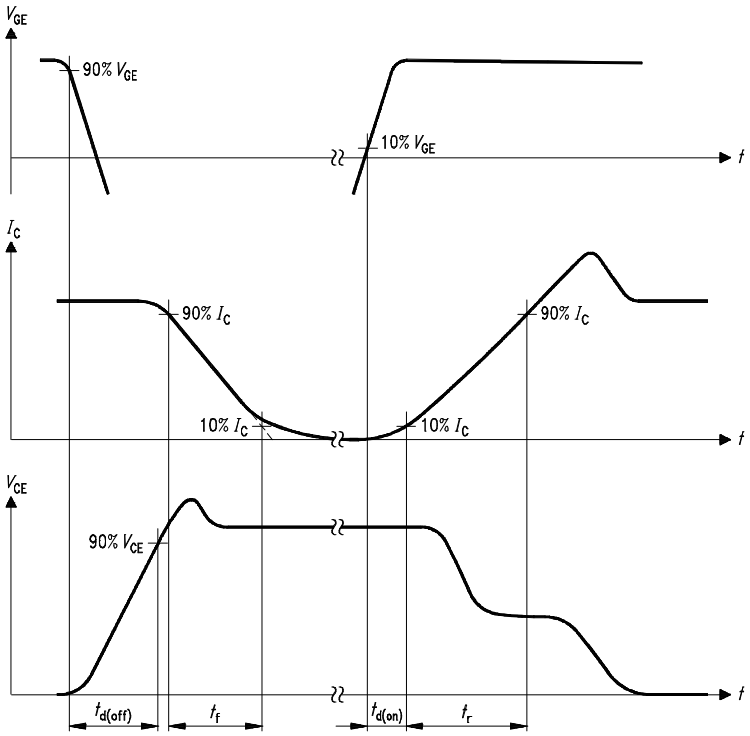


Figure A. Definition of switching times

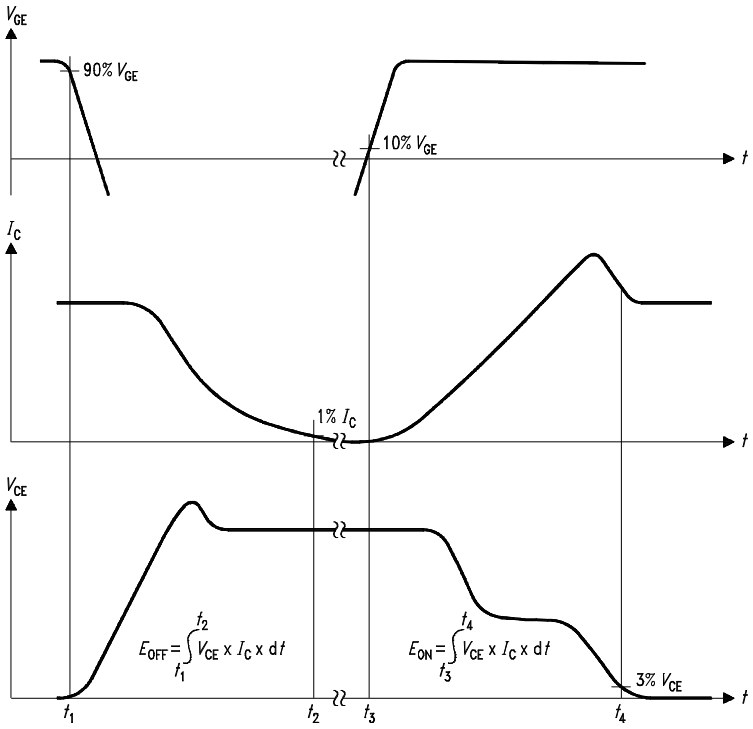


Figure B. Definition of switching losses

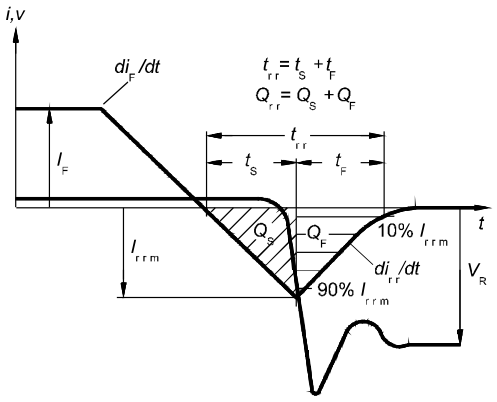


Figure C. Definition of diodes switching characteristics

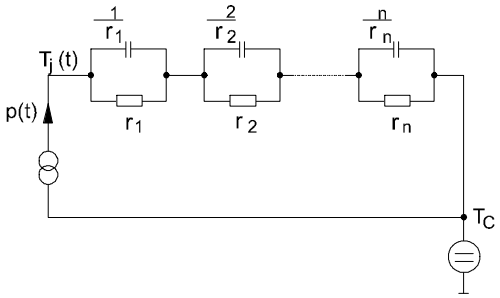


Figure D. Thermal equivalent circuit

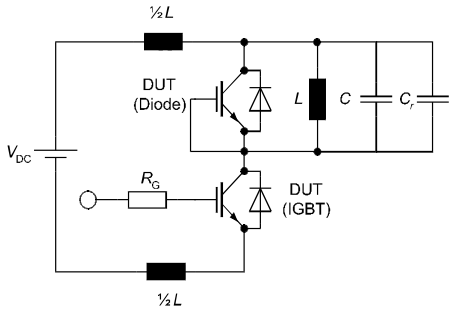


Figure E. Dynamic test circuit
Leakage inductance L= 180nH,
Stray capacitor C_o = 40pF,
Relief capacitor C_r = 1nF
(only for ZVT switching)

Published by
Infineon Technologies AG
81726 Munich, Germany
81726 München, Germany

Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

[1)] Rth/Zth based on single cooling pulse. Please be aware that a correct Rth measurement of this device, is not possible using a thermocouple.